DMP3098L

P-Channel Enhancement Mode MOSFET

Feature
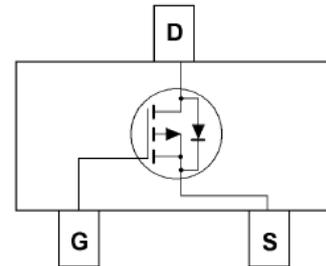
- -30V/-3.8A, $R_{DS(ON)}$ =55mΩ(MAX) @V_{GS} = -10V.

    $R_{DS(ON)}$ = 70mΩ(MAX) @V_{GS} = -4.5V.

    $R_{DS(ON)}$ =120mΩ(MAX) @V_{GS} = -2.5V.

- Super High dense cell design for extremely low $R_{DS(ON)}$
- Reliable and Rugged
- SOT-23 for Surface Mount Package

SOT-23

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-3.8	A

Electrical Characteristics T_A=25℃ Unless Otherwise noted

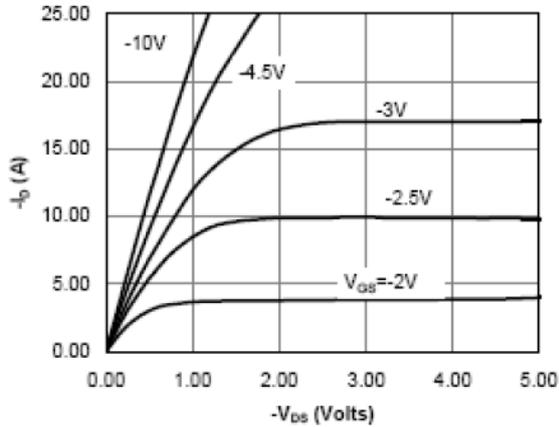| Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=-24V, VGS=0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=12V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-12V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-0.7	-	-1.3	V
Static Drain-source On-Resistance	RDS(ON)	VGS =-10V, ID =-4.2A	-	50	55	mΩ
		VGS =-4.5V, ID =-4.0A	-	60	70	mΩ
		VGS =-2.5V, ID =-1.0A	-	80	120	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.0A			-1.0	V

Typical Characteristics
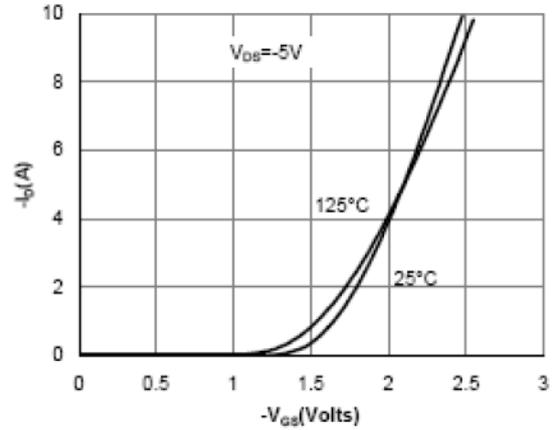

Fig 1: On-Region Characteristics
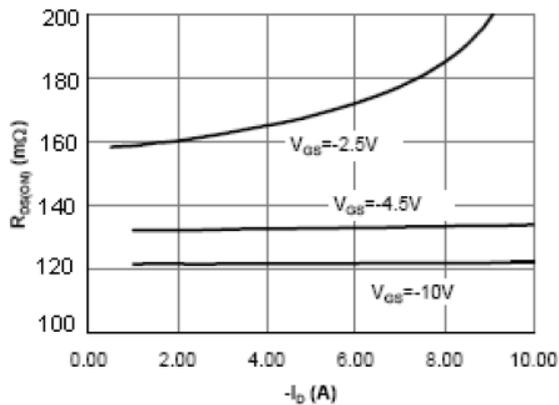

Figure 2: Transfer Characteristics

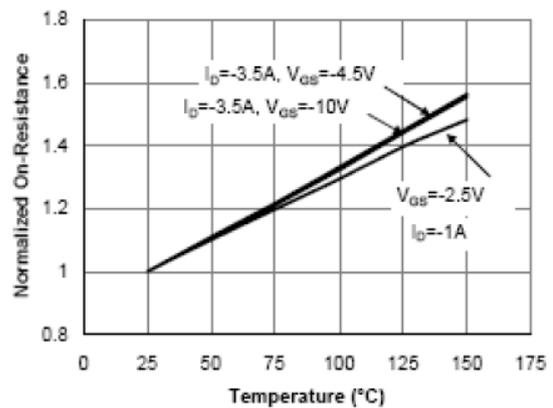Figure 3: On-Resistance vs. Drain Current and Gate Voltage

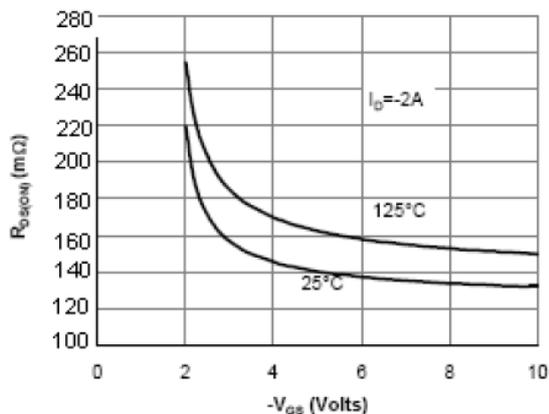Figure 4: On-Resistance vs. Junction Temperature

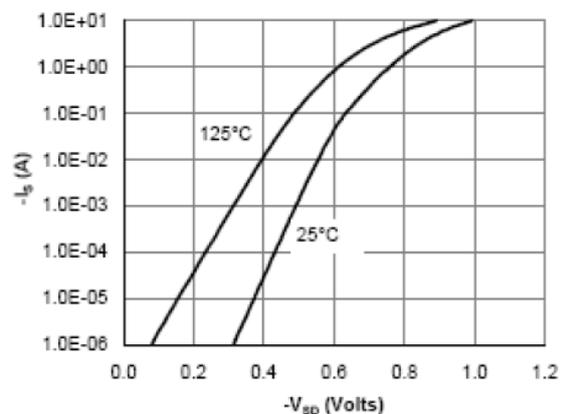Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

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